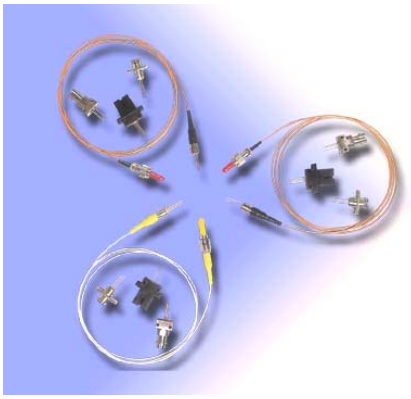
2.5Gbps InGaAs PIN Photodiode Module

Features

- High Responsivity
- High speed, typical 2.5GHz
- Low dark current, typical 0.1nA
- Low capacitance, typical 0.7pF
- Operating temperature range -40°C to 85°C
- Hermetically sealed TO-18 package in pigtailed or receptacle housing with FC, ST, SC, LC, MU or SMA connector



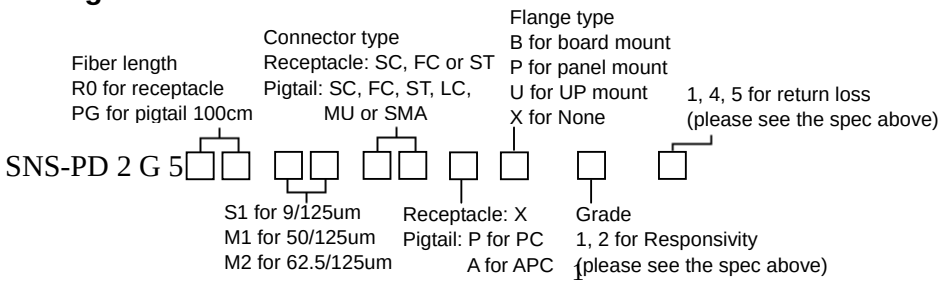
Specifications (T=25°C, -5V)

Parameter		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Responsivity		R					
9/125 um fiber	-1 -2		Laser source of 10 uw(λ=1300nm)	0.7 0.8	0.8 0.9	- -	A/W
50/125 um fiber	-1 -2		LED source of 10 uw(λ=1300nm)	0.65 0.75	0.75 0.85	- -	A/W
62.5/125 um fiber	-1 -2		LED source of 10 uw(λ=1300nm)	0.6 0.7	0.7 0.8	- -	A/W
Spectral Range			-	900	-	1600	nm
Dark Current		Id	V_R=2V, 0 to 1MHz	-	0.1	1	nA
Capacitance		Ct	V_R=2V, 1MHz	-	0.7	0.9	pF
Rise/fall Time		tr/tf	V_R=2V, 20% to 80%	-	<1	-	ns
Bandwidth		B		-	2.5	-	GHz
Return Loss							
-1(Receptacle)				14	-	-	dB
-3(Receptacle or Pigtail)				30			dB
-4(Receptacle or Pigtail)				40	-	-	dB
-5(Pigtail)				50	-	-	dB

Absolute Maximum Rating

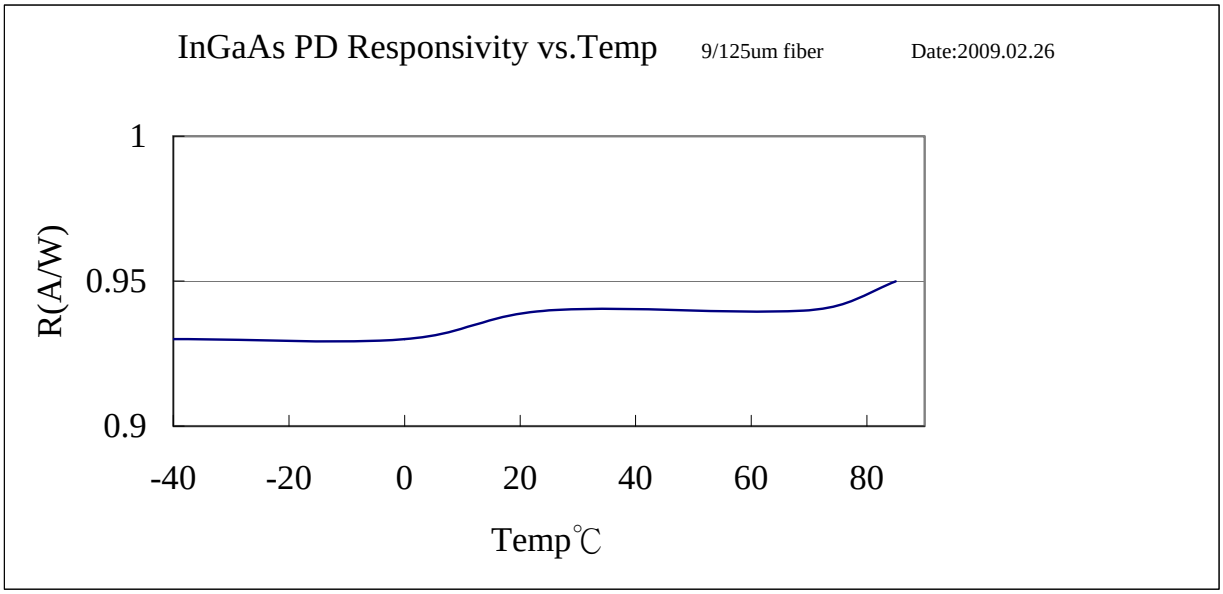
	Symbol	Min.	Max.	Unit
Operating Temperature	To	-40	+85	°C
Storage Temperature	T_{stg}	-40	+125	°C
Forward Current	I_F	-	5	mA
Reverse Voltage	V_R	-	30	V
Reverse Current	I_R	-	500	uA
Lead Soldering Temperature (10 sec)	T_L	-	260	°C

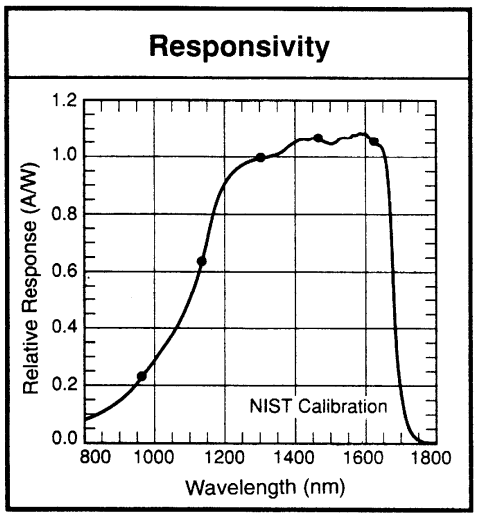
Ordering Information

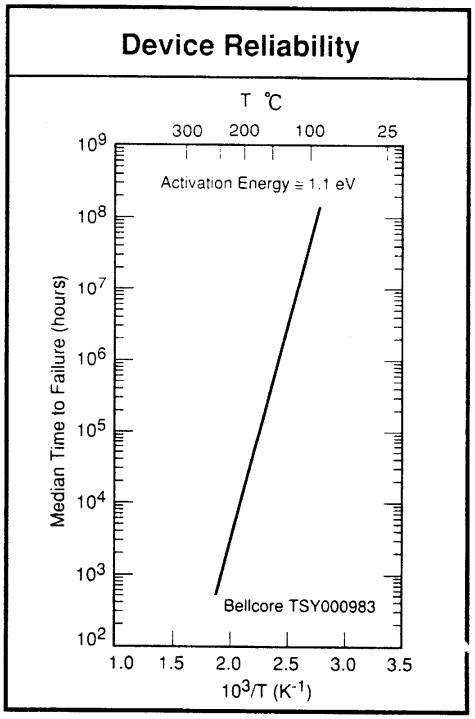
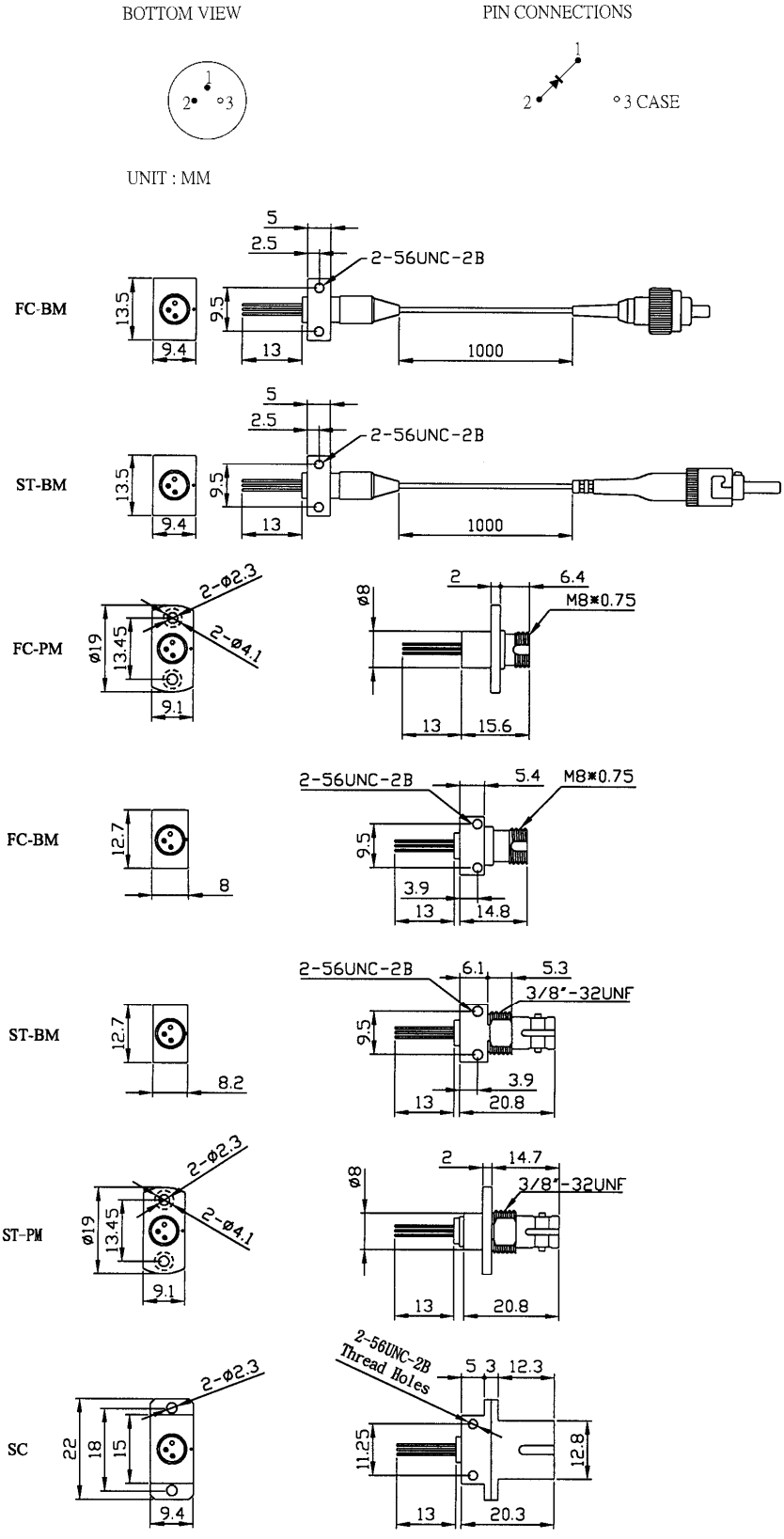


2009-03

2.5Gbps InGaAs PIN Photodiode Module







2.5Gbps InGaAs PIN Photodiode Module